

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(ON) \max}$ | $I_D \max$ $T_A = 25^\circ C$ |
|---------------|---------------------------------|----------------------------------|
| -20V | 54m Ω @ $V_{GS} = -4.5V$ | -2.5A |
| | 90m Ω @ $V_{GS} = -1.8V$ | -1.8A |

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

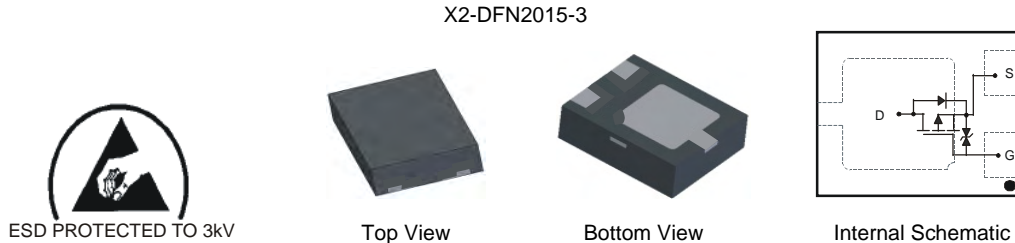
- Backlighting
- Power Management Functions
- DC-DC Converters
-

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 3kV**
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device, Halogen and Antimony Free (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: X2-DFN2015-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

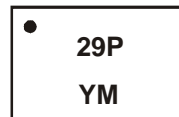


Ordering Information (Note 3)

| Part Number | Case | Packaging |
|---------------|--------------|------------------|
| DMP2069UFY4-7 | X2-DFN2015-3 | 3000/Tape & Reel |

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



29P = Marking Code
 YM = Date Code Marking
 Y = Year (ex: W = 2009)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 |
|------|------|------|------|------|------|------|------|
| Code | W | X | Y | Z | A | B | C |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | | | Symbol | Value | Units |
|-----------------------------------|--------------|-----------------------|------------------|-------|-------|
| Drain-Source Voltage | | | V _{DSS} | -20 | V |
| Gate-Source Voltage | | | V _{GSS} | ±8 | V |
| Continuous Drain Current (Note 4) | Steady State | T _A = 25°C | I _D | -2.5 | A |
| | | T _A = 70°C | | -2.2 | |
| Pulsed Drain Current (Note 5) | | | I _{DM} | -12 | A |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 4) | P _D | 0.53 | W |
| Thermal Resistance, Junction to Ambient @T _A = 25°C | R _{θJA} | 231 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|---------------------|------|-------|------|------|--|
| OFF CHARACTERISTICS (Note 6) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -20 | — | — | V | V _{GS} = 0V, I _D = -250μA |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | -1.0 | μA | V _{DS} = -20V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±10 | μA | V _{GS} = ±8V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 6) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -0.3 | -0.55 | -1.0 | V | V _{DS} = V _{GS} , I _D = -250μA |
| Static Drain-Source On-Resistance | R _{DS(ON)} | — | 36 | 54 | mΩ | V _{GS} = -4.5V, I _D = -2.5A |
| | | | 46 | 69 | | |
| | | | 60 | 90 | | |
| Forward Transfer Admittance | Y _{fs} | — | 8 | — | S | V _{DS} = -5V, I _D = -2.5A |
| DYNAMIC CHARACTERISTICS (Note 7) | | | | | | |
| Input Capacitance | C _{iss} | — | 214 | — | pF | V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz |
| Output Capacitance | C _{oss} | — | 104 | — | pF | |
| Reverse Transfer Capacitance | C _{rss} | — | 25 | — | pF | |
| Gate Resistor | R _g | — | 250 | — | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz |
| SWITCHING CHARACTERISTICS (Note 7) | | | | | | |
| Total Gate Charge | Q _g | — | 9.1 | — | nC | V _{GS} = -4.5V, V _{DS} = -10V, I _D = -4A |
| Gate-Source Charge | Q _{gs} | — | 1.5 | — | nC | |
| Gate-Drain Charge | Q _{gd} | — | 1.7 | — | nC | |
| Turn-On Delay Time | t _{D(on)} | — | 80.4 | 160 | ns | V _{DS} = -10V, V _{GS} = -4.5V, R _D = 2.5Ω, R _G = 3.0Ω |
| Turn-On Rise Time | t _r | — | 155.1 | 210 | ns | |
| Turn-Off Delay Time | t _{D(off)} | — | 688.1 | 1376 | ns | |
| Turn-Off Fall Time | t _f | — | 423.8 | 848 | ns | |

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

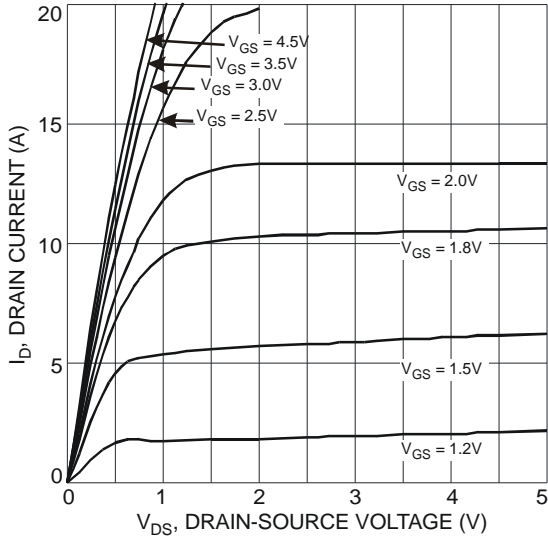


Fig. 1 Typical Output Characteristic

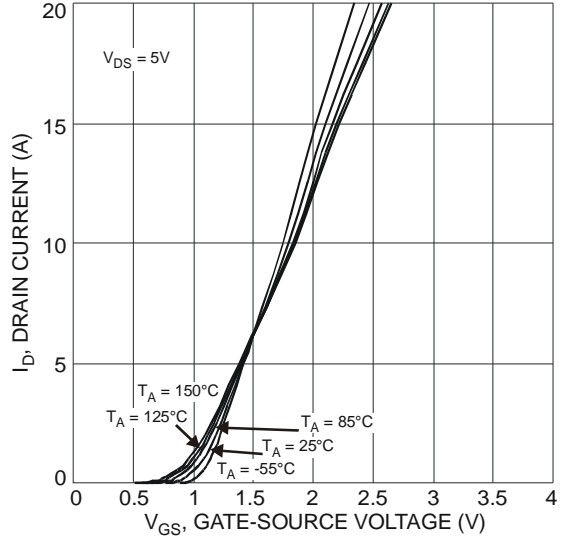


Fig. 2 Typical Transfer Characteristic

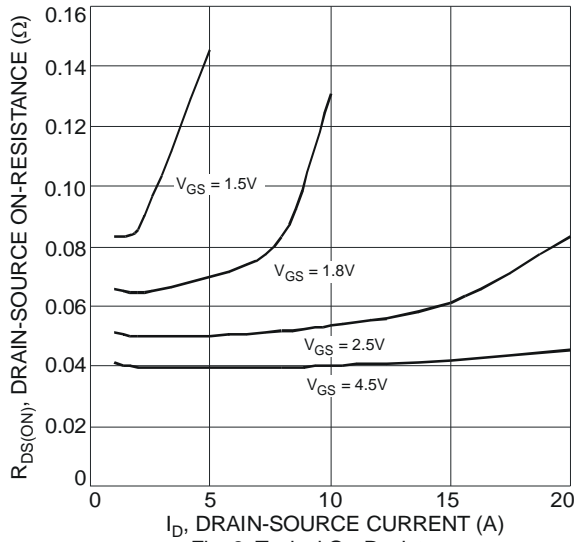


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

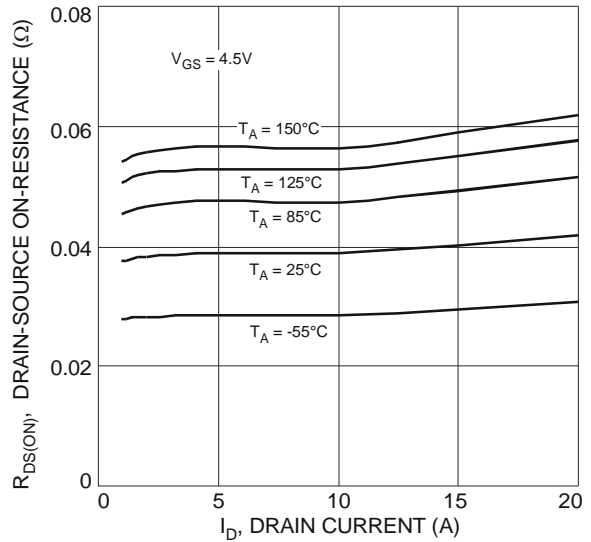


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

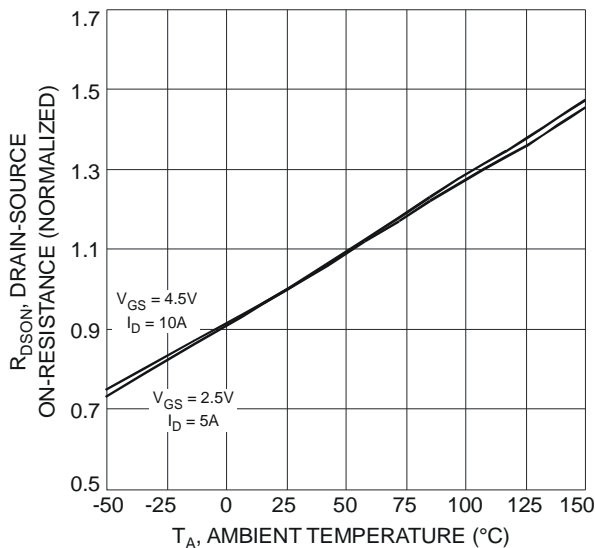


Fig. 5 On-Resistance Variation with Temperature

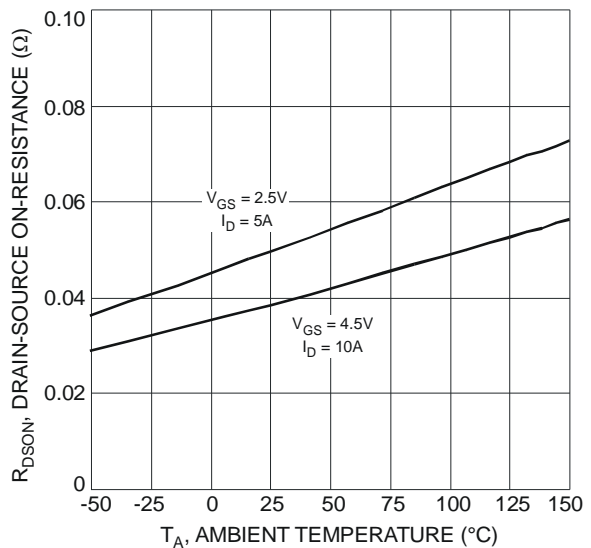


Fig. 6 On-Resistance Variation with Temperature

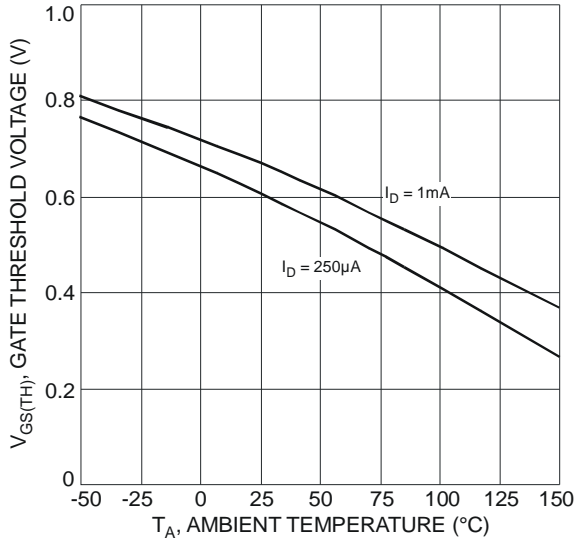


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

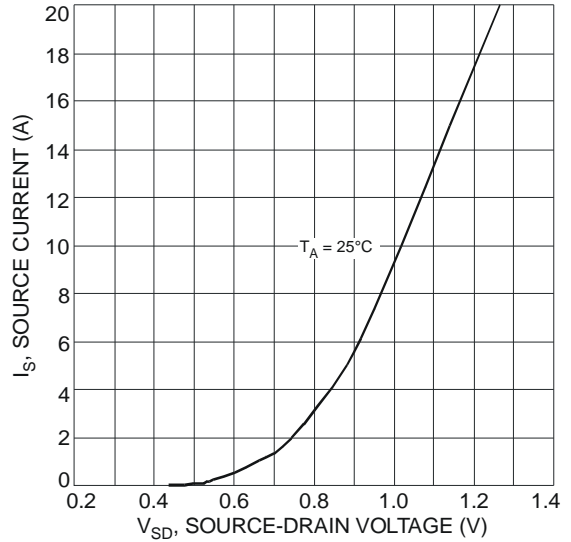


Fig. 8 Diode Forward Voltage vs. Current

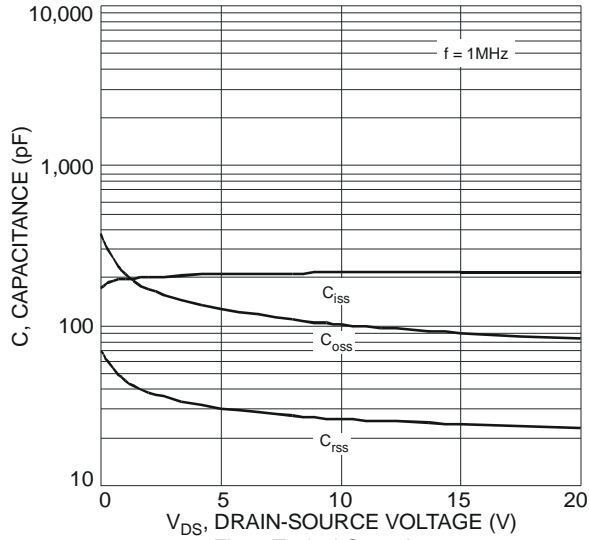


Fig. 9 Typical Capacitance

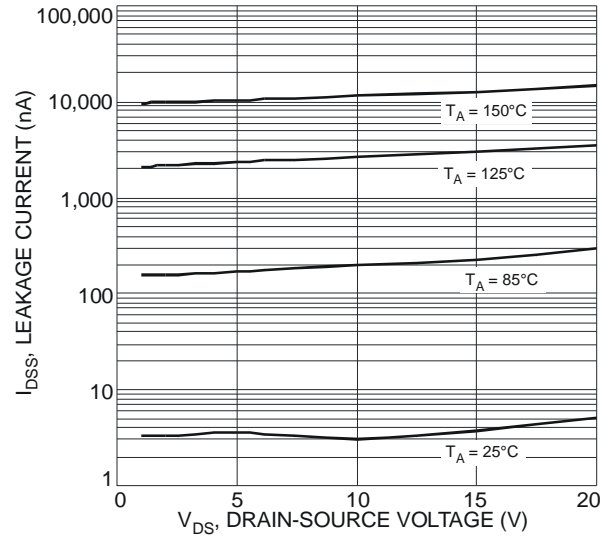


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

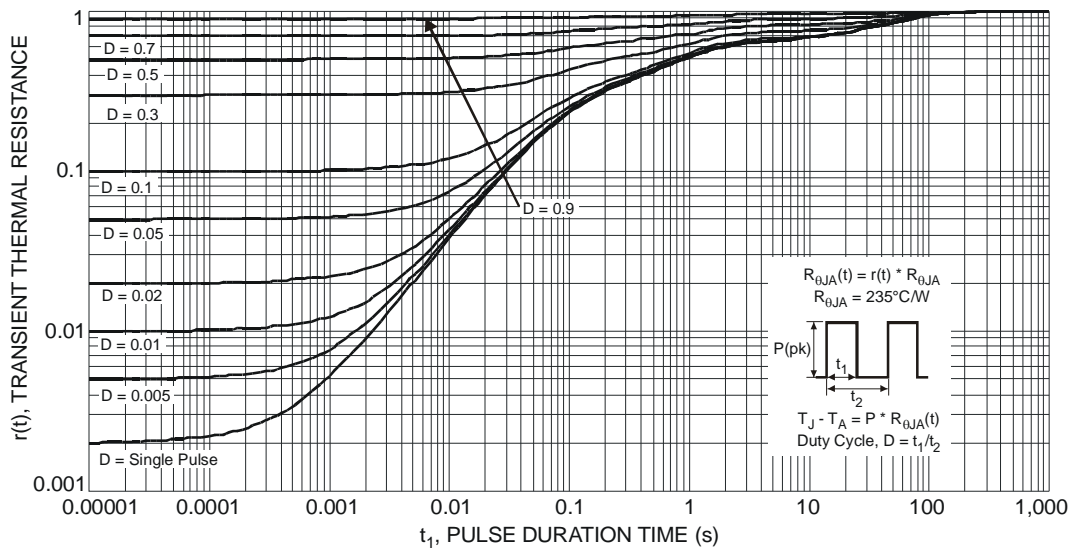
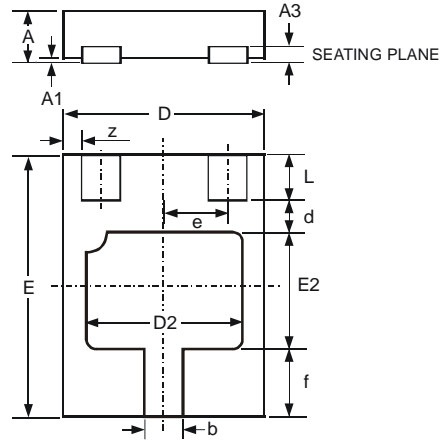


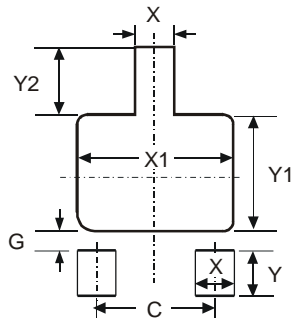
Fig. 11 Transient Thermal Response

Package Outline Dimensions



| X2-DFN2015-3 | | | |
|----------------------|------|-------|-------|
| Dim | Min | Max | Typ |
| A | - | 0.40 | - |
| A1 | 0 | 0.05 | 0.02 |
| A3 | - | - | 0.13 |
| b | 0.20 | 0.30 | 0.25 |
| d | - | - | 0.30 |
| D | 1.45 | 1.575 | 1.50 |
| D2 | 1.00 | 1.20 | 1.10 |
| e | - | - | 0.50 |
| E | 1.95 | 2.075 | 2.00 |
| E2 | 0.70 | 0.90 | 0.80 |
| f | - | - | 0.60 |
| L | 0.25 | 0.35 | 0.30 |
| z | - | - | 0.125 |
| All Dimensions in mm | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 1.00 |
| G | 0.15 |
| X | 0.31 |
| X1 | 1.30 |
| Y | 0.50 |
| Y1 | 1.00 |
| Y2 | 0.65 |

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